

MOSFET - Power, Single N-Channel

60 V, 62 mΩ, 11 A

NVLJWS070N06CL

Features

- Small Footprint for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	60	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D	A
		$T_C = 100^\circ\text{C}$	8	
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^\circ\text{C}$	P_D	W
		$T_C = 100^\circ\text{C}$	8	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	A
		$T_A = 100^\circ\text{C}$	3.1	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	P_D	W
		$T_A = 100^\circ\text{C}$	1.2	
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$	I_{DM}	31	A
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to +175	°C
Source Current (Body Diode)		I_S	13	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 0.4 \text{ A}$)		E_{AS}	17	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

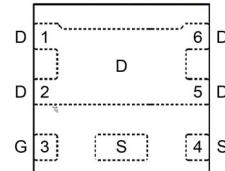
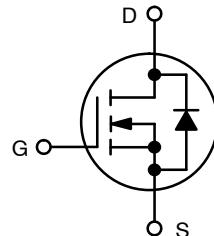
THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	9.8	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	63	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

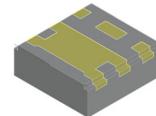
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
60 V	62 mΩ @ 10 V	11 A
	85 mΩ @ 4.5 V	

ELECTRICAL CONNECTION



(Top View)

N-CHANNEL MOSFET



MARKING
DIAGRAM



WDFNW6 (2.05x2.05)
CASE 515AD

070N = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVLJWS070N06CL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				26		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V	T _J = 25 °C			10	μA
			T _J = 125°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V				100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 6 μA		1.2		2.0	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-5.5		mV/°C
Drain-to-Source On Resistance	R _{DSS(on)}	V _{GS} = 10 V	I _D = 5 A		51	62	mΩ
		V _{GS} = 4.5 V	I _D = 5 A		68	85	
Forward Transconductance	g _F	V _{DS} = 10 V, I _D = 5 A			11		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		160		pF
Output Capacitance	C _{OSS}			81		
Reverse Transfer Capacitance	C _{rss}			2		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 48 V; I _D = 5 A	V _{GS} = 4.5 V, V _{DS} = 48 V; I _D = 5 A	8		nC
Total Gate Charge	Q _{G(TOT)}		V _{GS} = 10 V, V _{DS} = 48 V; I _D = 5 A	18		
Threshold Gate Charge	Q _{G(TH)}			1.8		
Gate-to-Source Charge	Q _{GS}			2.5		
Gate-to-Drain Charge	Q _{GD}			2.0		
Plateau Voltage	V _{GP}			2.2		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 48 V, I _D = 5 A, R _G = 6 Ω		4.4		ns
Rise Time	t _r			1.3		
Turn-Off Delay Time	t _{d(OFF)}			9.4		
Fall Time	t _f			1.3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 5 A	T _J = 25°C		0.91	1.2	V
			T _J = 125°C		0.81		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 5 A			16		ns
Charge Time	t _a				9		
Discharge Time	t _b				7		
Reverse Recovery Charge	Q _{RR}				7		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

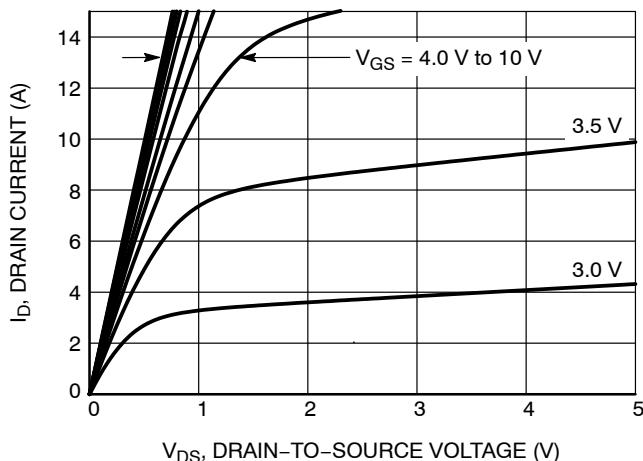


Figure 1. On-Region Characteristics

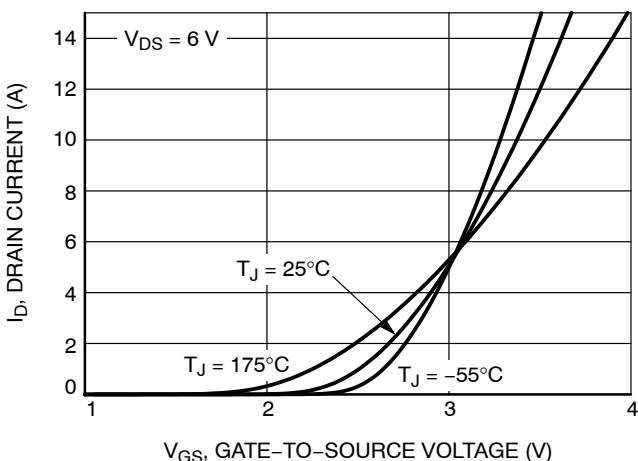


Figure 2. Transfer Characteristics

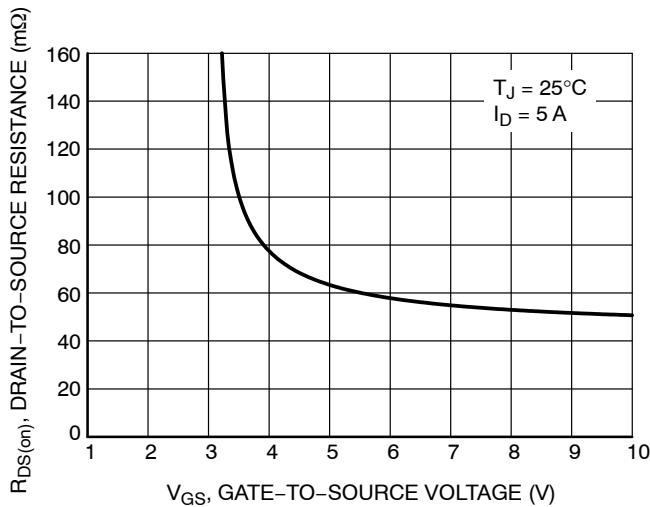


Figure 3. On-Resistance vs. Gate-to-Source Voltage

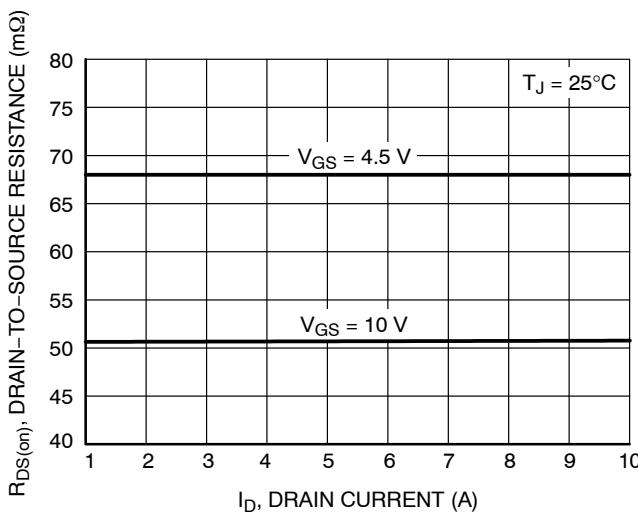


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

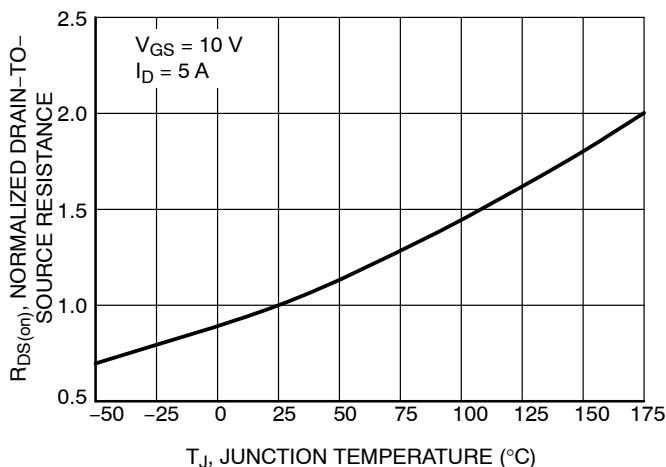


Figure 5. On-Resistance Variation with Temperature

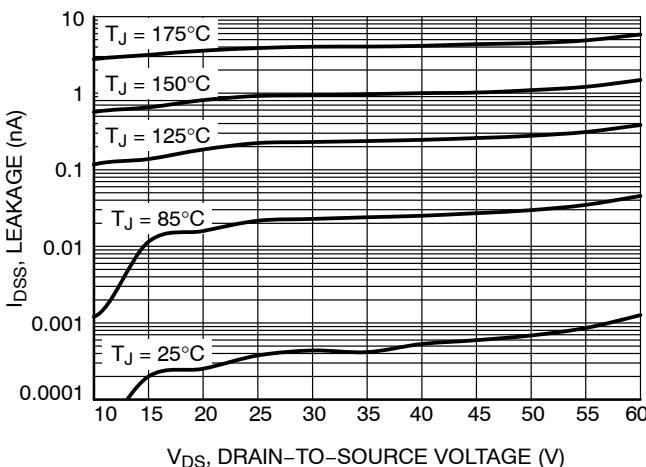
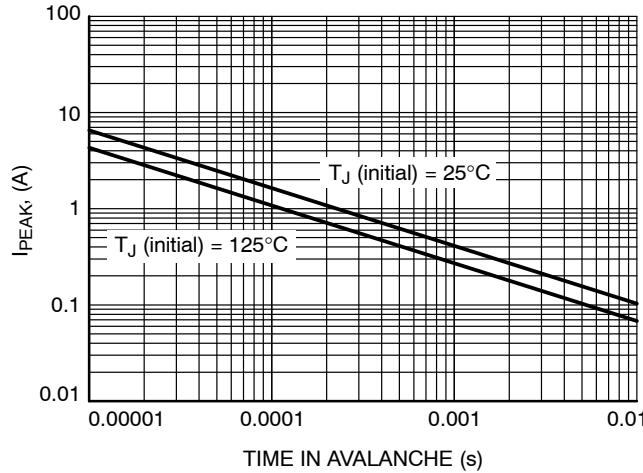
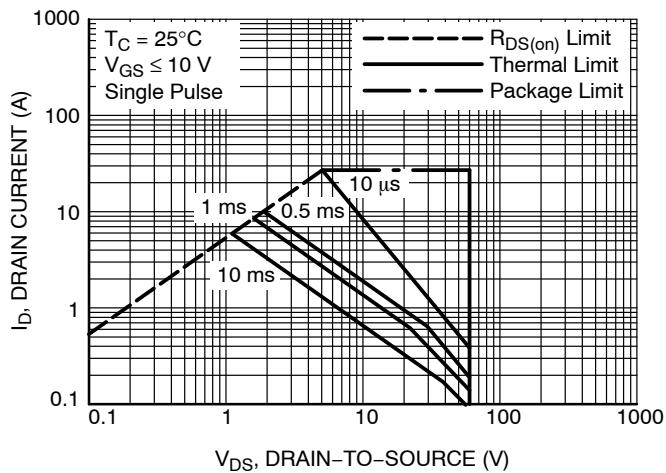
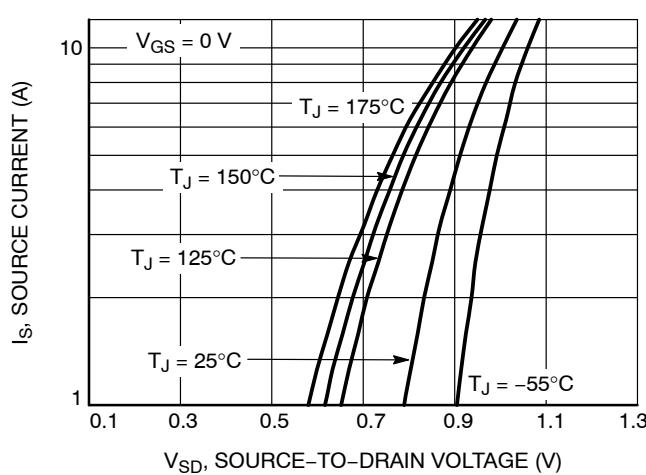
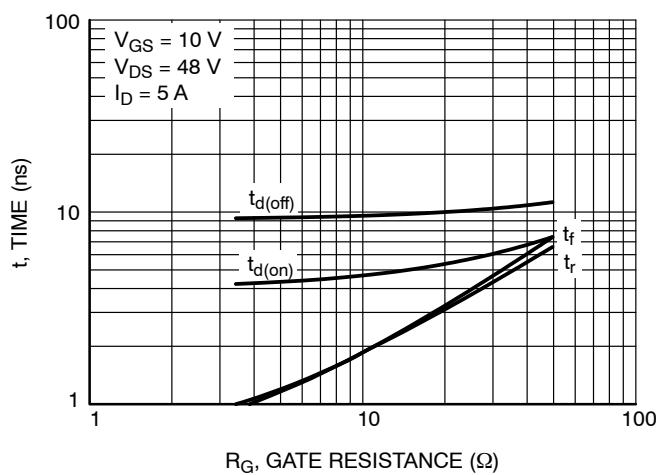
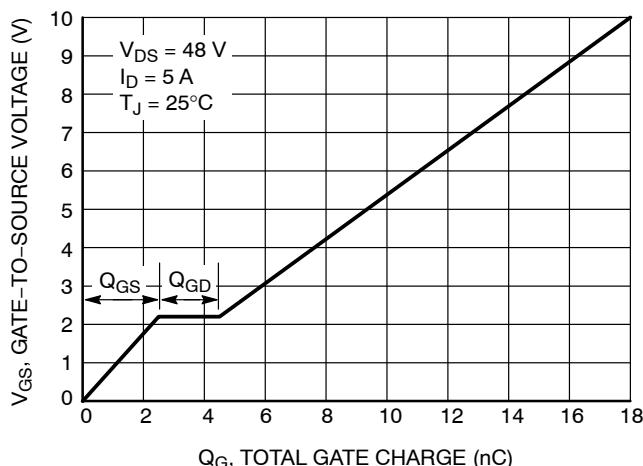
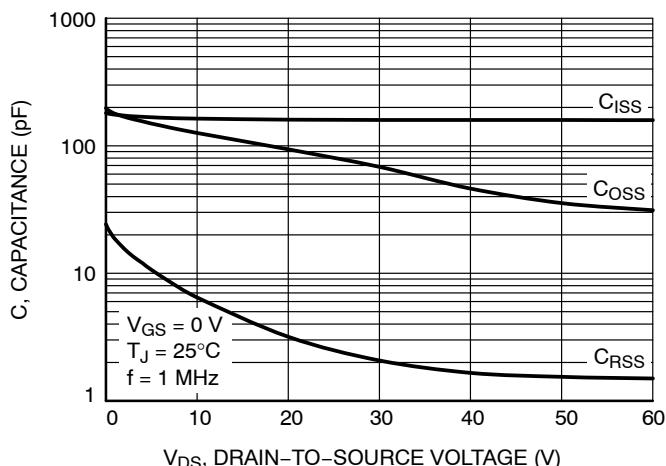


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

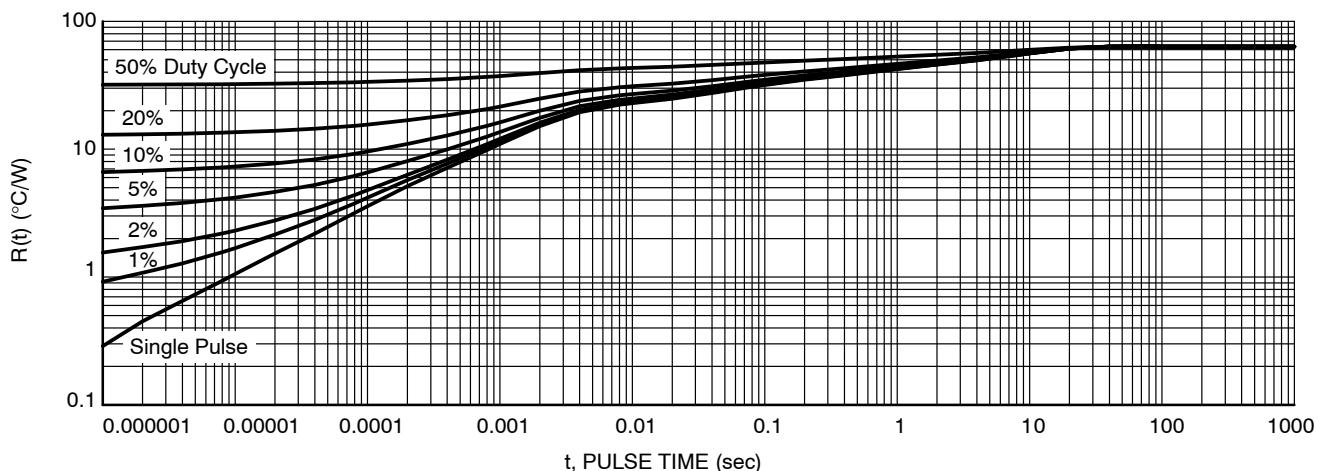


Figure 13. Transient Thermal Response Curve

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVLJWS070N06CLTAG	070N	WDFN6 (Pb-Free, Wettable Flanks)	3000 / Tape & Reel

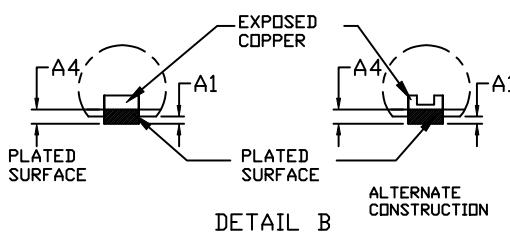
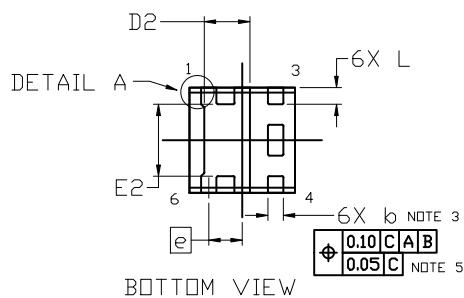
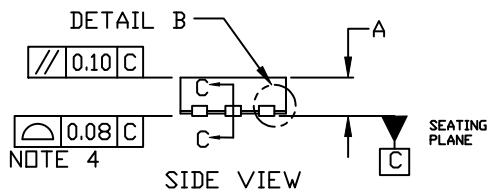
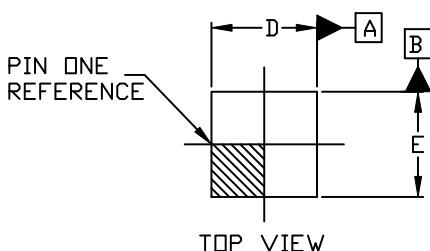
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

WDFNW6 2.05x2.05, 0.65P

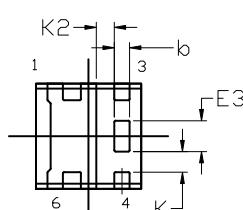
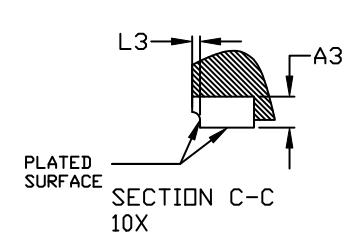
CASE 515AD

ISSUE O

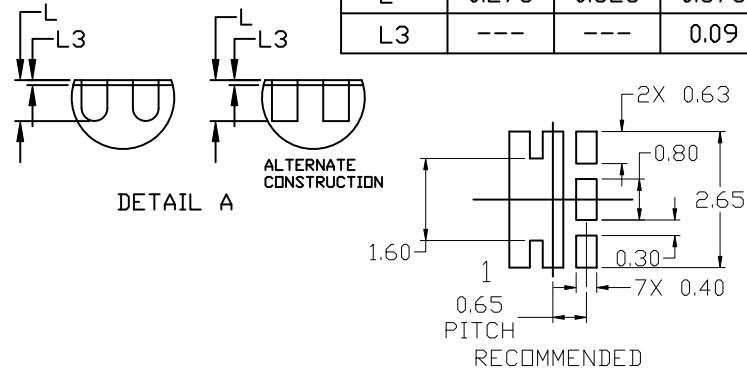


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. POSITIONAL TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	---	0.05
A3 0.20 REF			
A4	0.10	---	---
b	0.25	0.30	0.35
D	1.95	2.05	2.15
D2	0.84	0.89	0.94
E	1.95	2.05	2.15
E2	1.35	1.40	1.45
E3	0.55	0.60	0.65
e	0.65 BSC		
K	0.40 REF		
K2	0.35 REF		
L	0.275	0.325	0.375
L3	---	---	0.09



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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